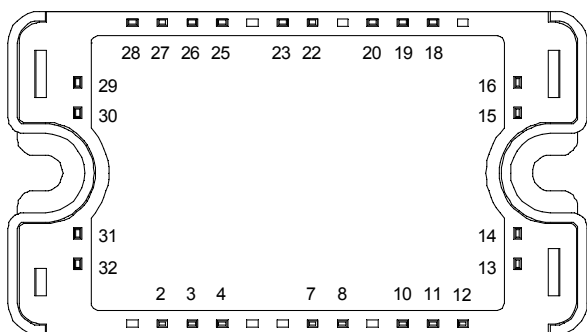
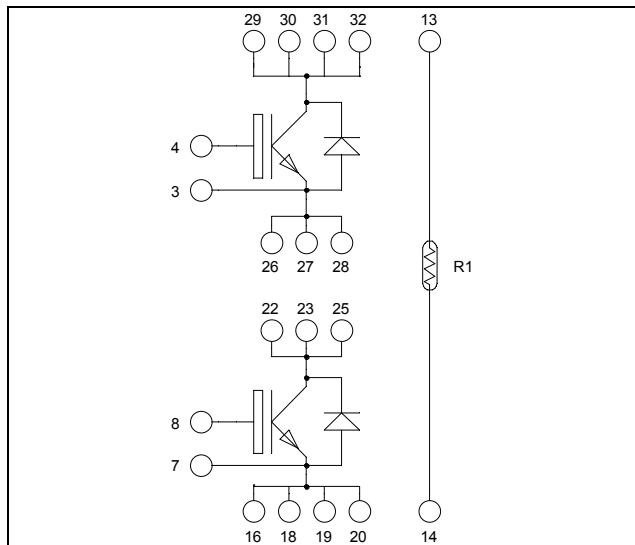


P

Phase leg Trench + Field Stop IGBT Power Module

$$V_{CES} = 1200V$$

$$I_C = 150A @ T_c = 100^{\circ}C$$



Pins 29/30/31/32 must be shorted together

Pins 26/27/28/22/23/25 must be shorted together
to achieve a phase leg

Pins 16/18/19/20 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Kelvin emitter for easy drive
- Internal thermistor for temperature monitoring
- High level of integration
- AlN substrate for improved thermal performance

Benefits

- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^{\circ}C$	A
		$T_C = 100^{\circ}C$	
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	300
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	833
RBSOA	Reverse Bias Safe Operating Area	$T_J = 125^{\circ}C$	300A @ 1150V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 150A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.7 2.0	2.1	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 3\text{ mA}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		10.7		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		0.56		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.48		
Q_G	Gate charge	$V_{GE} = \pm 15V; V_{CE} = 600V$ $I_C = 150A$		1.4		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 150A$ $R_G = 2.2\Omega$		280		ns
T_r	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			420		
T_f	Fall Time			75		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 150A$ $R_G = 2.2\Omega$		290		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			520		
T_f	Fall Time			90		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 150A$ $R_G = 2.2\Omega$	$T_j = 125^\circ\text{C}$	14		mJ
E_{off}	Turn-off Switching Energy		$T_j = 125^\circ\text{C}$	16		
I_{sc}	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 900V$ $t_p \leq 10\mu\text{s}; T_j = 125^\circ\text{C}$		600		A

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		350 600	μA
I_F	DC Forward Current		$T_c = 100^\circ\text{C}$	150		A
V_F	Diode Forward Voltage	$I_F = 150A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.6 1.6	2.1	V
t_{rr}	Reverse Recovery Time	$I_F = 150A$ $V_R = 600V$ $di/dt = 2500A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	170		ns
			$T_j = 125^\circ\text{C}$	280		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	14 28		μC
			$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	6 11		
E_r	Reverse Recovery Energy					mJ

Thermal and package characteristics

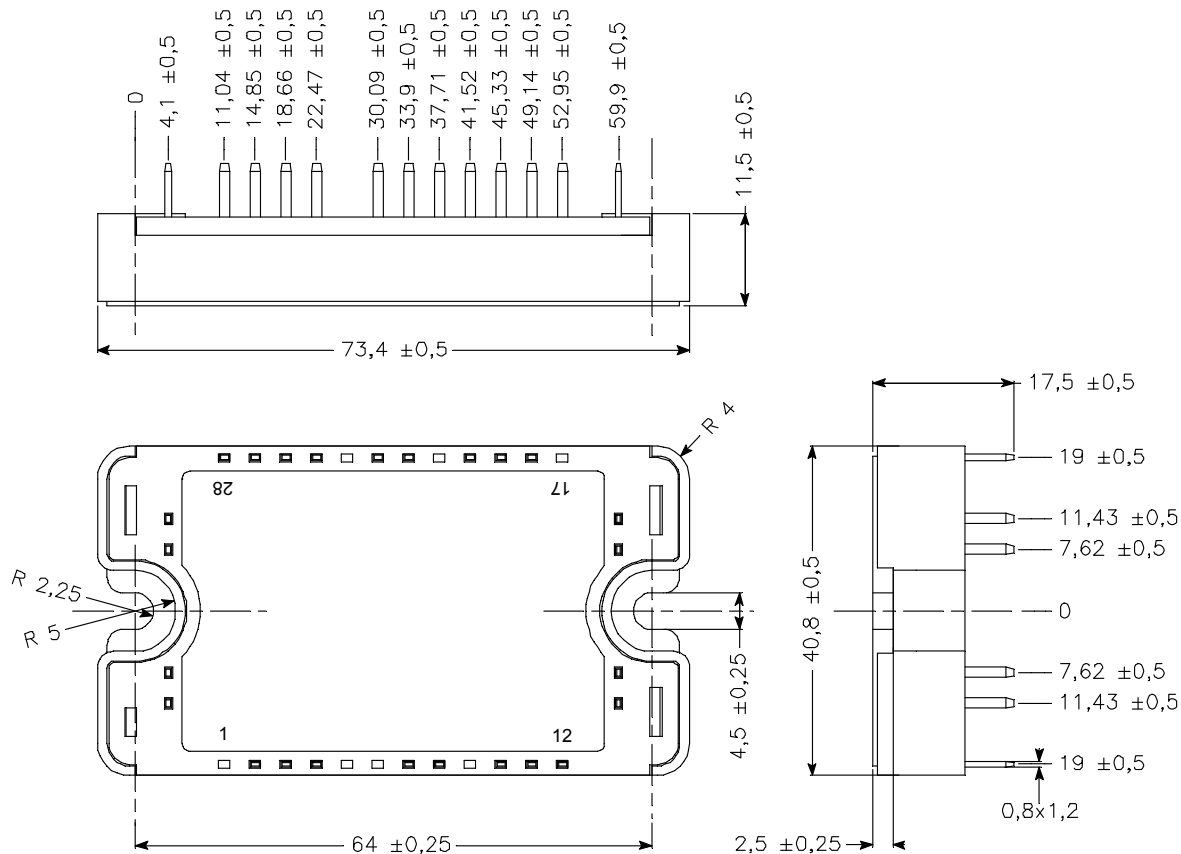
Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		IGBT			0.15	°C/W
			Diode			0.25	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2.5		4.7	N.m
Wt	Package Weight					110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C =100°C		4		%

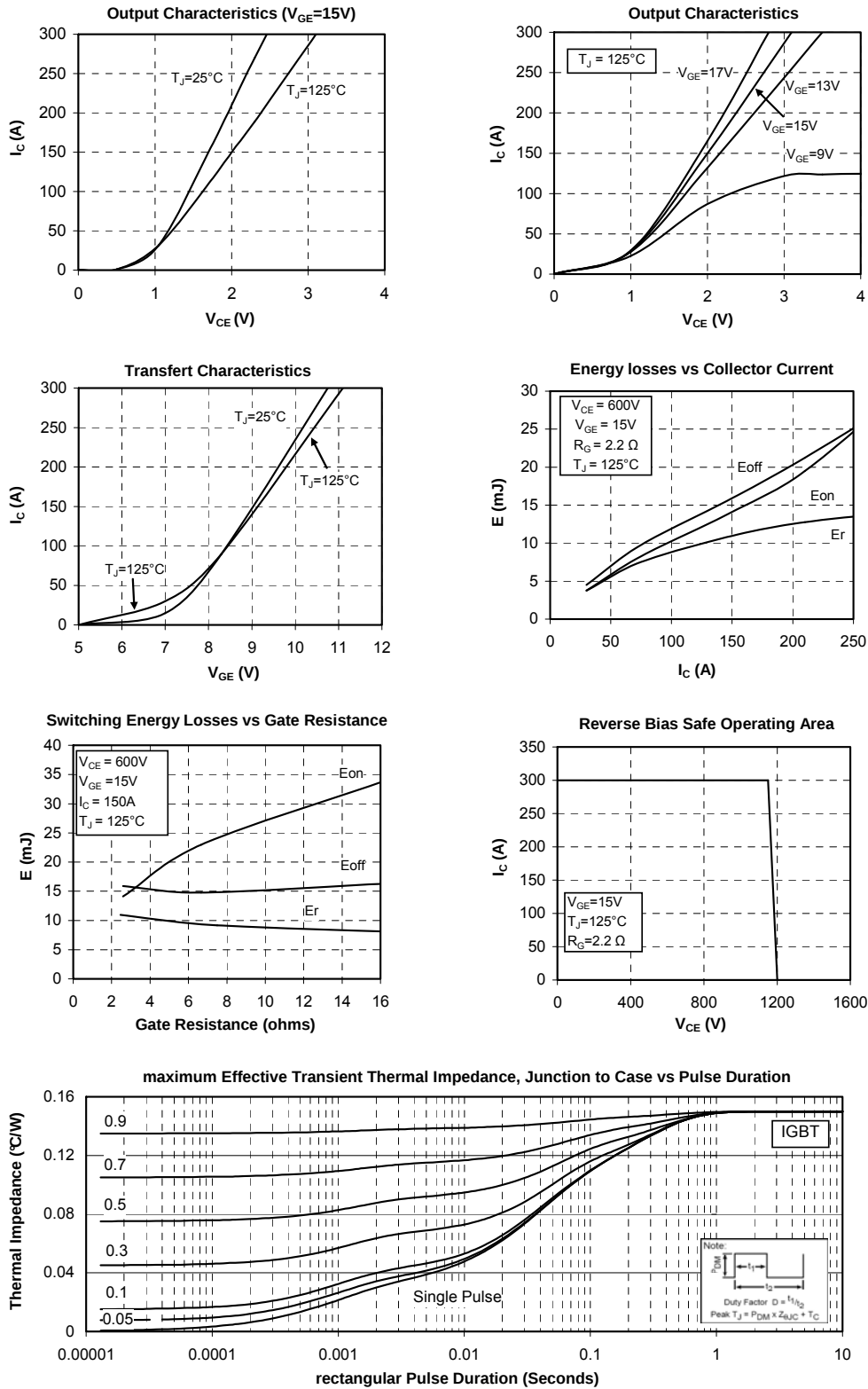
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

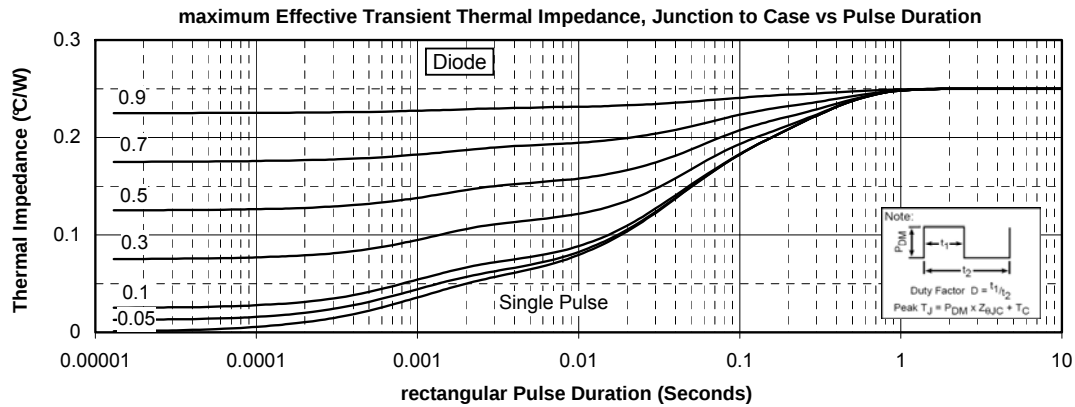
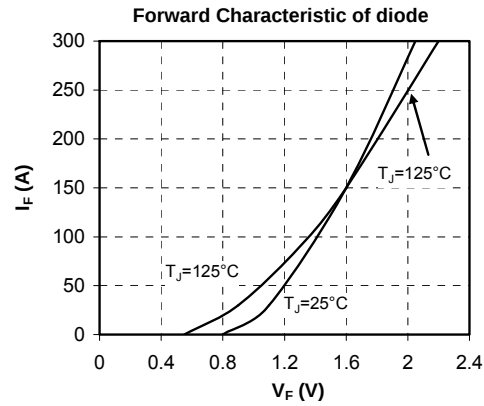
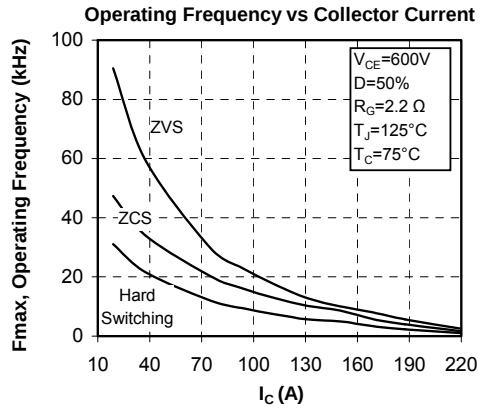
SP3 Package outline (dimensions in mm)



See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.